



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



企业QQ二维码

Features

- $BV_{CEO} > 120V$
- $BV_{CBO} > 140V$
- $I_C = 1.5A$ High Continuous Current
- $h_{FE} > 2k$ for High Gain @ 1A

Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.112 grams (Approximate)

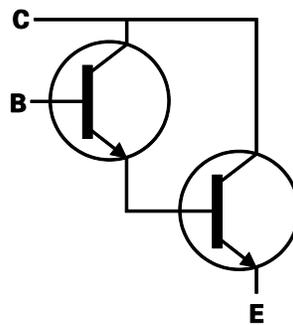
Applications

- Lamp
- Relay
- Solenoid Driving

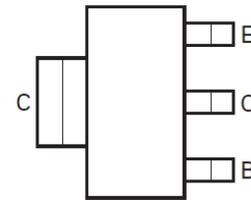
SOT223 (Type DN)



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	140	V
Collector-Emitter Voltage	V _{CEO}	120	V
Emitter-Base Voltage	V _{EBO}	14	V
Continuous Collector Current	I _C	1.5	A
Peak Pulse Current	I _{CM}	4	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

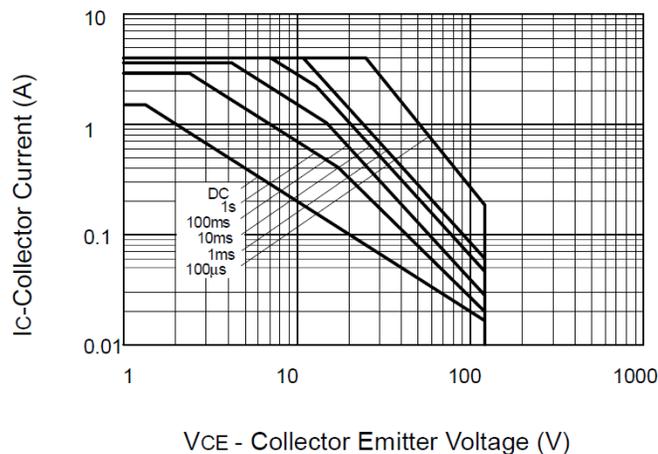
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 5)	3.0
		(Note 6)	2.0
		(Note 7)	1.6
		(Note 8)	1.2
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 5)	41.7
		(Note 6)	62.5
		(Note 7)	78.1
		(Note 8)	104
Thermal Resistance Junction to Lead	R _{θJL}	12.9	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 10)

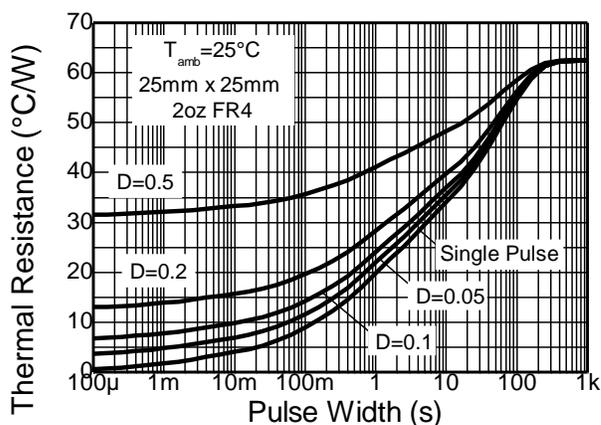
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 - Same as Note 5, except the device is mounted on minimum recommended pad layout.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

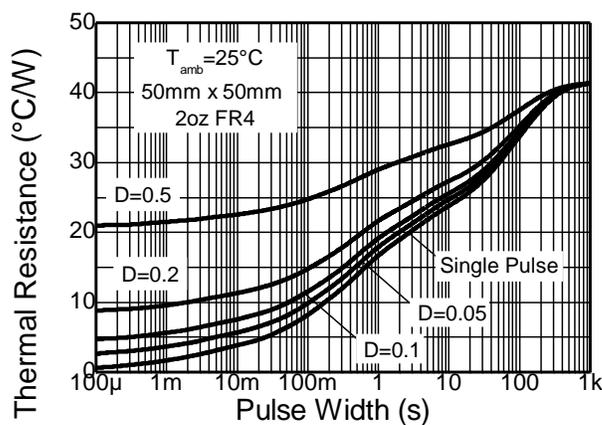
Thermal Characteristics and Derating Information



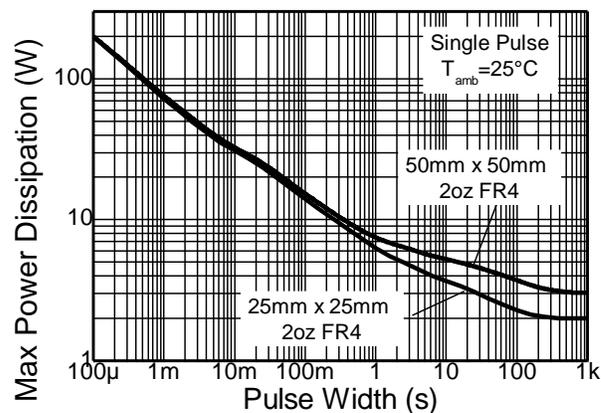
FZT605 Safe Operating Area



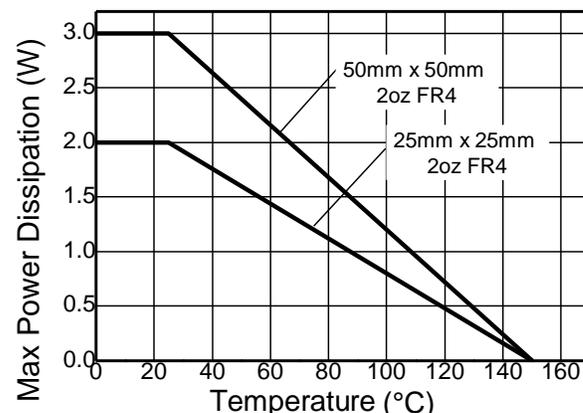
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



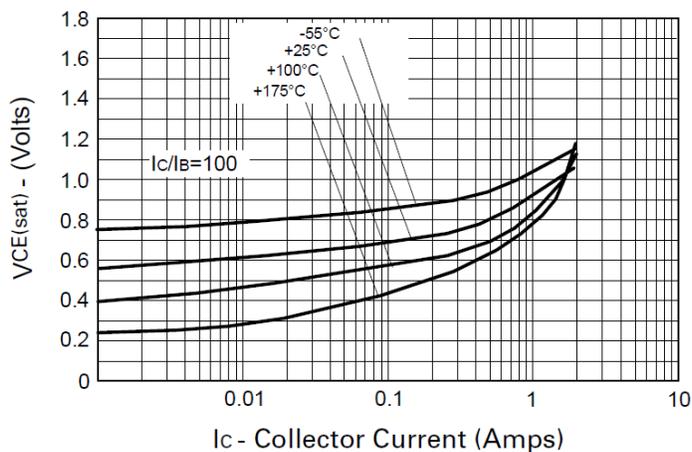
Derating Curve

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

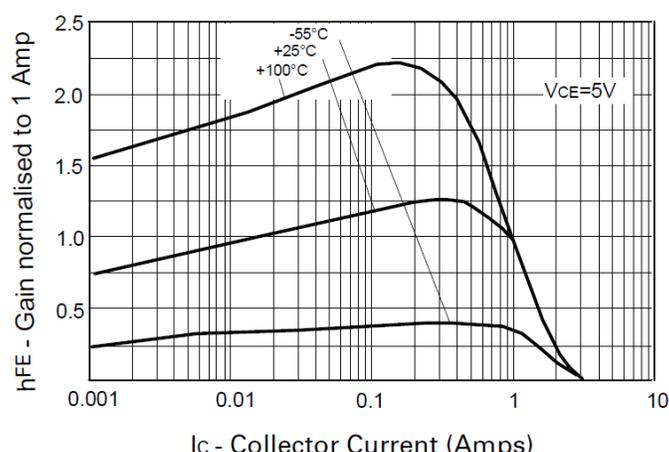
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CB0}	140	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	120	—	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	14	—	—	V	$I_E = 100\mu\text{A}$
Collector-Base Cut-Off Current	I_{CBO}	—	—	100 10	nA μA	$V_{CB} = 120\text{V}$ $V_{CB} = 120\text{V}, T_A = +120^\circ\text{C}$
Collector-Emitter Cut-Off Current	I_{CES}	—	—	100	nA	$V_{CE} = 120\text{V}$
Emitter Cut-Off Current	I_{EBO}	—	—	100	nA	$V_{EB} = 8\text{V}$
DC Current Gain (Note 11)	h_{FE}	2,000 5,000 2,000 500	— — — —	— — 100,000 —	—	$I_C = 50\text{mA}, V_{CE} = 5\text{V}$ $I_C = 500\text{mA}, V_{CE} = 5\text{V}$ $I_C = 1\text{A}, V_{CE} = 5\text{V}$ $I_C = 2\text{A}, V_{CE} = 5\text{V}$
Collector-Emitter Saturation Voltage (Note 11)	$V_{CE(sat)}$	— —	— —	1 1.5	V	$I_C = 250\text{mA}, I_B = 0.25\text{mA}$ $I_C = 1\text{A}, I_B = 1\text{mA}$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	—	—	1.8	V	$I_C = 1\text{A}, I_B = 1\text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	—	—	1.7	V	$I_C = 1\text{A}, V_{CE} = 5\text{V}$
Input Capacitance	C_{ibo}	—	90	—	pF	$V_{EB} = 0.5\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{obo}	—	15	—	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Current Gain-Bandwidth Product	f_T	150	—	—	MHz	$V_{CE} = 10\text{V}, I_C = 100\text{mA}$ $f = 20\text{MHz}$
Turn-On Time	t_{on}	—	0.5	—	μs	$V_{CC} = 10\text{V}, I_C = 500\text{mA}$
Turn-Off Time	t_{off}	—	1.6	—	μs	$I_{B1} = -I_{B2} = 0.5\text{mA}$

 Note: 11. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

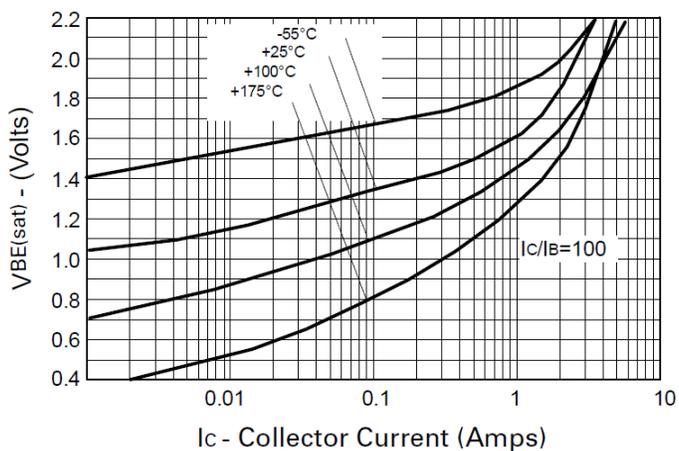
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



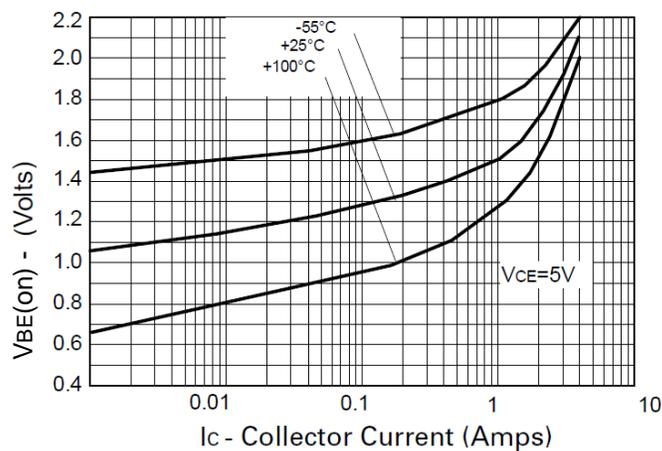
$V_{CE(sat)}$ v I_C



h_{FE} v I_C



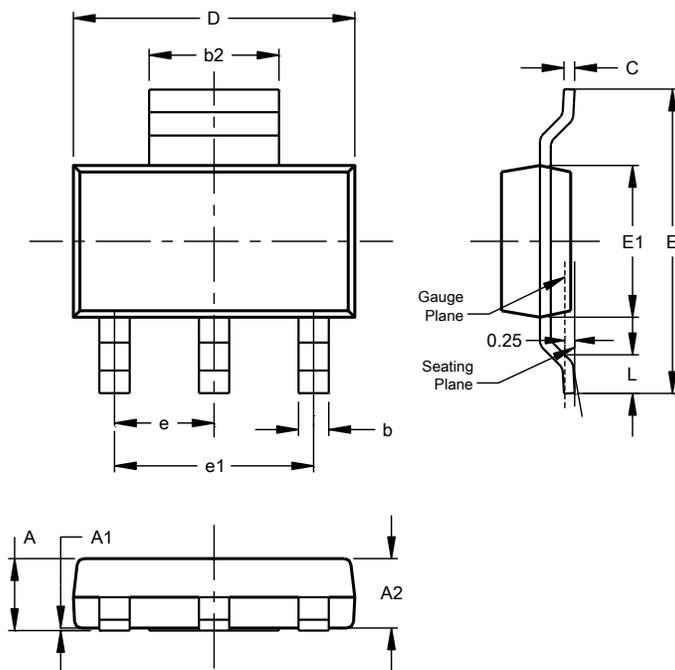
$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C

Package Outline Dimensions

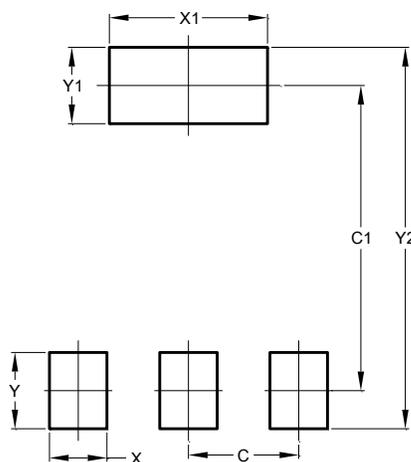
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Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00